

IN THE SPECIFICATION:

Page 6, delete the whole paragraph [0024] and replace it with the following new paragraph:

[0024] Plasma processing system 50 may be any one of a number of plasma processing systems, such as an electrostatically shielded radio frequency (ESRF) plasma system, as shown in FIG. 1A. Such plasma processing systems are described in U.S. Patents No. ~~4,938,031~~ 4,918,031 and 5,234,529, which patents are incorporated herein by reference. Thus, in an exemplary embodiment of system 50, plasma source generator 80 includes an inductive coil 90 that encircles a portion of chamber 60 so as to surround upper region 65U. Inductive coil 90 may be a helical resonator (i.e. a quarter-wave or half-wave resonator), wherein one coil end is grounded, and the opposite coil end is open. Coil 90 is tapped near the grounded end, whereby the coil is electrically connected to an RF power supply 92 through a match network 92MN. The latter is used to maximize RF power transfer to plasma 82. Between inductive coil 90 and chamber wall 62 is a grounded electrostatic shield 98 (also referred to as an E-shield or Faraday shield) comprising an electrically grounded, conductive sheet with slots (not shown) aligned parallel with the axis of revolution A (i.e., the central axis) of chamber 60 (i.e., in the vertical or Y-direction) and are typically equally spaced. E-shield 98 minimizes capacitive coupling between coil 90 and plasma 82 by limiting the area through which the electromagnetic field from the coil can couple to the plasma. Furthermore, the wall 64 additionally includes a dielectric window (not shown) proximate the inductive coil 90 in order to allow the penetration of the RF electromagnetic field into the plasma. Other plasma source configurations can include capacitively coupled plasma (CCP) sources, electron cyclotron resonance (ECR) plasma sources, helicon-type plasma sources, etc., without limiting the scope of the present invention.